

**I. AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1-42. (Canceled)

1 43. (New) In a process for manufacturing a semiconductor device that has performance  
2 characteristics that may vary during the initial period of operation, a method for  
3 stabilizing the device comprising:

- 4 a. applying a test current to the semiconductor device for a brief period of time; and  
5 b. repeating step (a) above at an incremental current over the test current until the test  
6 current is above the normal operating current of the semiconductor device.

1 44. (New) The method of claim 43, further comprising providing an elevated ambient  
2 temperature for the semiconductor device during the steps of providing a sequence of  
3 test currents.

1 45. (New) The method of claim 44, wherein the dwell time of each application of a test  
2 current is about 15 ms.

1 46. (New) The method of claim 43, wherein the number of cycles of providing a test  
2 current is about four.

1 47. (New) The method of claim 43, wherein the semiconductor device is a vertical  
2 cavity surface emitting laser and the step of providing a test current to said semiconductor  
3 device further includes sequentially providing a sequence of test currents, to each of the  
4 vertical cavity surface emitting lasers on a wafer under test.

- 1 48. (New) The method of claim 43, wherein the scan current ramp rate, the number of
- 2 scans per device, the dwell time, the peak value of input current, and the ambient
- 3 temperature are adjusted for each process.